

ABSTRACT OF THE DISCLOSURE

On a given silicon substrate is epitaxially grown a strain-relaxed silicon germanium layer with penetrated dislocations and formed a metallic layer to form a multilayered intermediate structure, which is heated. In this case, metallic elements of the metallic layer are diffused through the penetrated dislocations of the silicon germanium layer to form a thin line structure made of metallic silicide at a boundary face between the silicon base and the silicon germanium layer.